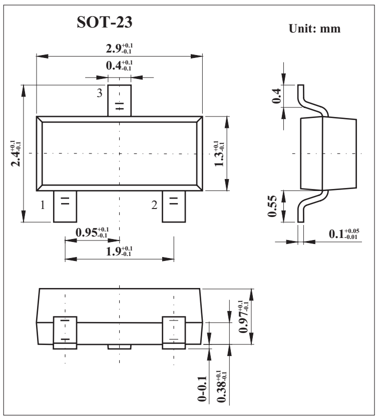
Silicon PIN Diodes

BA779;BA779S

■ Features

- ● Wide frequency range 10 MHz to 1 GHz



■ Absolute Maximum Ratings Ta = 25℃

Parameter	Symbol	Test Conditions	Value	Unit
Reverse Voltage	V_R		30	V
Forward Current	I_F		50	mA
Junction Temperature	T_j		125	℃
Storage temperature range	T_{stg}		-55 to +125	℃
Junction ambient	R_{thJA}	on PC board 50mm×50mm×1.6mm	500	K/W

■ Electrical Characteristics Ta = 25℃

Parameter		Symbol	Conditions	Min	Typ	Max	Unit
Forward Voltage		V_F	I_F = 20 mA			1	V
Reverse Current		I_R	V_R = 30 V			50	nA
Diode capacitance		C_D	f = 100 MHz, V_R = 0			0.5	pF
Differential forward resistance		r_f	f = 100 MHz, I_F = 1.5 mA			50	Ω
Reverse impedance	BA799 BA799S	z_r	f = 100 MHz, V_R = 0	5 9			KΩ
Minority carrier lifetime		τ	I_F = 10 mA, I_R = 10 mA		4		μS